Attorney Docket No: 0492611-0545/MIT-9277CONII

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Seleznev, et al.	Examiner:	Cooke
Serial No.:	10/799,388	Art Unit:	1754
Filing Date:	March 12, 2004		
Title:	VACUUM PROCESSING FOR FABRICATION OF SUPERCONDUCTING THIN FILMS FABRICATED BY METAL-ORGANIC PROCESSING		

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first-class mail in an envelope addressed to: Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450, on June 3, 2005.

Susan M. Dinsmore

Susan M. Dinsmore

STATEMENT FILED PURSUANT TO THE DUTY OF DISCLOSURE UNDER 37 CFR §§1.56, 1.97 AND 1.98

Pursuant to the duty of disclosure under 37 C.F.R. §§1.56, 1.97 and 1.98, Applicants respectfully request consideration of this Information Disclosure Statement.

PART I: Compliance with 37 C.F.R. §1.97

(Select A, B or C below)

A. [ ] This Information Disclosure Statement has been filed:
(check 1, 2 and/or 3 below)

1. [ ] within three months of the filing date of the above identified U.S. Patent application;

2. [ ] within three months of the filing date of the entry of the National Stage, as set forth in 37 C.F.R. §1.491, in an International application; and/or

3. [ ] before the mailing date of the first Office Action on the merits in the above-identified application.

No fee or certification is required.

B. [X] This Information Disclosure Statement has been filed more than three months after the filing date of the present application and after the mailing date of this first Office Action, but before the mailing date of either a final action under 37 C.F.R. §1.113 or a Notice of Allowance under 37 C.F.R. §1.311.

(check 1 or 2 below)

1. [X] The fee of $180 as set forth in 37 C.F.R. §1.17(p) is enclosed; or
2. [ ] Applicants hereby certify, as specified in 37 C.F.R. §1.97(e), that

(check a or b below)

a. [ ] each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign Patent Office in a counterpart for this application not more than three months prior to the filing of this Statement; or

b. [ ] no item of information contained in this Information Disclosure Statement was cited in a communication from a foreign Patent Office in a counterpart for this application or, to the knowledge of the undersigned after making reasonable inquiry, was known to any individual designated in 37 C.F.R. §1.56(c) more than three months prior to the filing of this Statement.

c. [] items indicated by an asterisk were identified in a recent review of related files.

C. [ ] This Information Disclosure Statement has been filed after the mailing date of either a Final action under 37 C.F.R. §1.113 or a Notice of Allowance under 37 C.F.R. §1.311 and before payment of an Issue Fee.

(check 1, 2, and 3 below)

1. [ ] The Applicant hereby certifies, as specified in 37 C.F.R. §1.97(e), that:

(check a or b below)

a. [ ] each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign Patent Office in a counterpart for this application not more than three months prior to the filing of this Statement.

b. [ ] no item of information contained in this Information Disclosure Statement was cited in a communication from a foreign Patent Office in a counterpart for this application or, to the knowledge of the undersigned after making reasonable inquiry, was known to any individual designated in 37 C.F.R. §1.56(c) more than three months prior to the filing of this Statement.

2. [ ] A Petition requesting consideration of the Information Disclosure Statement is attached.

3. [ ] The Petition Fee of $130 as set forth in 37 C.F.R. §1.17(i)(1) is enclosed.

PART II - Information Cited

A. [X] The Applicant hereby makes of record in the above-identified application the reference(s) listed on the attached form PTO-1449 (modified). The order of presentation of the references should not be construed as an indication of the importance of the references.

B. [ ] The Applicant hereby makes the following additional information of record in the above-identified application:

PART III: Explanation of Non-English Language References and Remarks Concerning Other Information Cited

A. [ ] The following is a concise explanation of the relevance of each non-English language reference listed on the attached form PTO-1449 (modified):

B. [ ] The following are remarks concerning the other information cited:

PART IV: Remarks

A. [X] Copies of references

(check 1 or 2 below)

1. [X] A copy of each of the references cited on the attached form PTO-1449 (modified) is enclosed, except for U.S. patents and U.S. patent application publications for which the submission requirement has been waived by the PTO in the Official Gazette Notice of August 5, 2003, for applications filed after June 30, 2003.

2. [X] Copies of certain of the references cited on the attached form PTO-1449 (modified) are not enclosed because each of these references (indicated by asterisk) was previously cited by or submitted to the Office in a prior application, U.S.S.N. 10/194,561, which prior application is relied upon for an earlier filing date under 35 U.S.C. § 120.

B. [X] It is respectfully requested that:

(check 1, 2, and 3 below)

1. [X] The Examiner consider completely the cited information, along with any other information, in reaching a determination concerning the patentability of the present claims;

2. [X] The enclosed form PTO-1449 be signed by the Examiner to evidence that the cited patent(s) and publication(s) has (have) been fully considered by the Patent and Trademark Office during the examination of this application;

3. [X] The citations for the patent(s) and publication(s) be printed on any patent which issues from this application.

C. [X] By submitting this Information Disclosure Statement, Applicants make no representation that a search has been performed, of the extent of any search performed, or that more material information may not exist.

D. [X] By submitting this Information Disclosure Statement, Applicants make no representation that the information cited in the Statement is, or is considered to be, material to patentability as defined in 37 C.F.R. §1.56(b).

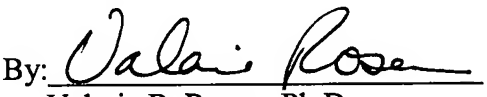
E. [X] By submitting this Information Disclosure Statement, Applicants make no representation that the information cited in the Statement is, or is considered to be, in fact, prior art as defined by 35 U.S.C. §102.

F. [X] Notwithstanding any statements by Applicants, the Examiner is urged to form his or her own conclusions regarding the relevance of the cited reference(s).

An early and favorable action is hereby requested.

Please charge any additional fees or credit any overpayments to our Deposit Account No. 03-1721.

Respectfully submitted,

By: 

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Form PTO-1449 (REV. 8-83) U.S. Department of Commerce Patent and Trademark Office		Atty. Docket: 0492611-0545/MIT-9277CONII	In re Application No. 10/799,388
		Applicant: Seleznev, *et al.*	
INFORMATION DISCLOSURE STATEMENT (*Use several sheets if necessary*)		Filing Date: March 12, 2004	Group: 1754

U.S. PATENT DOCUMENTS

Examiner's Initials	U.S. Patent No.	Applicant	Issue Date	Class	Subclass
	4,931,425	Kimura, et al.	June, 1990		
	4,959,346	Mogro-Campero, et al.	September 25, 1990	505	1
	5,143,898	Takano, et al.	September 1, 1992	505	1
	5,225,561	Kirlin, et al.	July, 1993		
	5,231,074	Cima, et al.	July 27, 1993	505	1
	5,280,012	Kirlin, et al.	January, 1994		
	5,296,460	Wessels, et al.	March, 1994		
	5,306,698	Ahn, et al.	April 26, 1994	505	475
	5,308,800	Wehrle, et al.	May 3, 1994	505	400
	5,319,118	Norman, et al.	June, 1994		
	5,453,494	Kirlin, et al.	September, 1995		
	5,603,983	Clough, et al.	February, 1997		
	5,661,114	Otto, et al.	August 26, 1997	505	501
	5,741,377	Goyal, et al.	April 21, 1998	148	512
	5,850,098	Butler, et al.	December 15, 1998	257	467
	5,854,587	Horwitz, et al.	December 29, 1998	338	22
	5,856,277	Chen, et al.	January 5, 1999	505	452
	5,972,847	Feenstra, et al.	October 26, 1999	505	473
	6,172,009	Smith, et al.	January 9, 2001	505	473
	6,486,100	Lee, et al.	November 26, 2002	505	470
	6,673,387	Zhang, et al.	January 6, 2004	427	62

U.S. PATENT APPLICATIONS

Examiner's Initials:	Serial Number:	Applicant:	Filing Date:	Group:	Art Unit:
	2002/0182451	Smith, et al.	December 5, 2002		

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	2003/0050195	Wiesmann, et al.	March 13, 2003		
	2005/0014052	Seleznev, et al.	January 20, 2005		

FOREIGN PATENT DOCUMENTS

Examiner's Initials	Document No.	Country	Date	Translation	
				Yes	No
	WO 96/32201	PCT	October 17, 1996		

OTHER DOCUMENTS

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	Berkowitz, et al., "Increased Transition Temperature in *in situ* Coevaporated $YBa_2Cu_3O_{7-\delta}$ Thin Films by Low Temperature Post-annealing", *Appl. Phys. Lett.* **65** 1587-1589 (1994)
	Chan, et al., "Effect of the post-Deposition Processing Ambient on the Preparation of Superconducting $YBa_2Cu_3O_{7-x}$ Coevaporated Thin Films Using a BaF_2 Source", *Appl. Phys. Lett.* **53** 1443-1445 (1988)
	*Cima, et al., "Conversion Kinetics of Oxyfluoride-Derived YBCO Films", *Materials Research Society Fall Conference*, November 28-December 3, 1999
	de Obaldia, et al., "Coexistence of Grains With Differing Orthorhombicity in High Quality $YBa_2Cu_3O_{7-\delta}$ Thin Films", *Appl. Phys. Lett.* **65** 3395-3397 (1994)
	DeSantolo, et al., "Preparation of High T_c and J_c Films of $Ba_2YCu_3O_7$ Using Laser Evaporation of a Composite Target Containing BaF_2", *Appl. Phys. Lett.* **52** 1995-1997 (1988)
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	Krause, Carolyn, "Hot Wire: ORNL's Promising Route to Superconductivity", *Oak Ridge National Laboratory Review* **29** 2-7 (1996)
	Mankiewich, et al., "High Critical-Current Density $Ba_2YCu_3O_7$ Thin Films Produced by Coevaporation of Y_1 Cu_1 and BaF_2", *High Temperature Superconductivity* 1 18a-18g (1986-1988)
	Mankiewich, et al., "Preparation and Processing of Thin Film $Ba_2YCu_3O_7$", *High Temperature Superconductivity* **1** 17a-17q (1986-1988)
	Mankiewich, et al., "Reproducible Technique for Fabrication of Thin Films of High Transition Temperature Superconductors", *High Temperature Superconductivity* **1** 19a-19c (1986-1988)

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	McIntyre, et al., "Effect of Growth Conditions on the Properties and Morphology of Chemically Derived Epitaxial Thin Films of $Ba_2YCu_3O_{7-x}$ on (001) $LaAlO_3$", *J. Appl. Phys.* **71** 1868-1877 (1992)
	McIntyre, et al., "Epitaxial Nucleation and Growth of Chemically Derived $Ba_2YCu_3O_{7-x}$ Thin Films on (001) $SrTiO_3$", *J. Appl. Phys.* **77** 5263-5272 (1995)
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	U.S. Department of Energy's Superconductivity Program for Electric Systems 1996 Annual Peer Review, July 31 and August 1, 1996
	U.S. Department of Energy's 1997 Wire Development Workshop, February 6-7, 1997
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	Young, et al., "Superconductivity in the Fluorinated YBaCuO", *Mat. Res. Soc. Symp. Proc.* **99** 549-552 (1988)		

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